

Description

The AR0521D5 is a bi-directional TVS diode, utilizing leading monolithic silicon technology to provide fast response time and low ESD clamping voltage, making this device an ideal solution for protecting voltage sensitive high-speed data lines. The AR0521D5 has an ultra-low capacitance with a typical value at 0.3pF, and complies with the IEC 61000-4-2 (ESD) with ±25kV air and ±22kV contact discharge. It is assembled into a SOD-523 lead-free package. The small size, ultra-low capacitance and high ESD surge protection make AR0521D5 an ideal choice to protect cell phone, digital visual interfaces and other high speed ports.

Features

• Ultra low capacitance: 0.3pF typical

Ultra low leakage: nA levelOperating voltage: 5V

• Low clamping voltage

Complies with following standards:

IEC 61000-4-2 (ESD) immunity test
 Air discharge: ±25kV
 Contact discharge: ±22kV

- IEC61000-4-5 (Lightning) 4A (8/20µs)

RoHS Compliant

Mechanical Characteristics

Package: SOD-523Lead Finish: Matte Tin

• Case Material: "Green" Molding Compound.

Moisture Sensitivity: Level 3 per J-STD-020

Terminal Connections: See Diagram Below

Marking Information: See Below

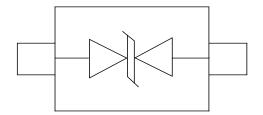
Applications

- Cellular Handsets and Accessories
- Display Ports
- MDDI Ports
- USB Ports
- Digital Visual Interface (DVI)
- PCI Express and Serial SATA Ports

Marking Information



Ordering Information Dimensions and Pin Configuration



Circuit and Pin Schematic

Part Number	Packaging	Reel Size
AR0521D5	3000/Tape & Reel	7 inch



Absolute Maximum Ratings (T_A=25°C unless otherwise specified)

Parameter	Symbol	Value	Unit	
Peak Pulse Power (8/20µs)	Ppk	100	W	
Peak Pulse Current (8/20µs)	IPP	4	Α	
ESD per IEC 61000-4-2 (Air)	\/rop	±25	1-7.7	
ESD per IEC 61000-4-2 (Contact)	VESD	±22	kV	
Operating Temperature Range	TJ	−55 to +125	°C	
Storage Temperature Range	Tstg	−55 to +150	°C	

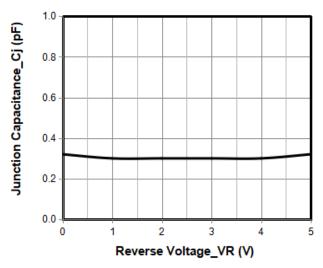
Electrical Characteristics (T_A=25°C unless otherwise specified)

Parameter	Symbol	Min	Тур	Max	Unit	Test Condition
Reverse Working Voltage	VRWM			5	V	
Breakdown Voltage	VBR	6.5		9.5	V	IT = 1mA
Reverse Leakage Current	I _R		0.02	0.2	μA	VRWM = 5V
Clamping Voltage	Vc			12	V	IPP = 1A (8 x 20μs pulse)
Clamping Voltage	Vc			25	V	IPP = 4A (8 x 20μs pulse)
Junction Capacitance	CJ		0.3	0.5	pF	VR = 0V, f = 1MHz

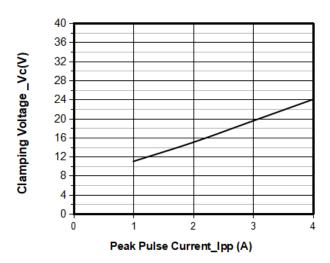
Revision, 12/2017 2 of 4



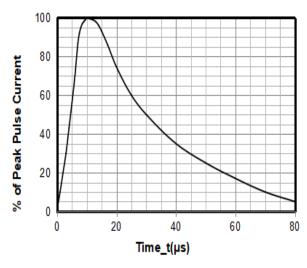
Typical Performance Characteristics (TA=25°C unless otherwise Specified)



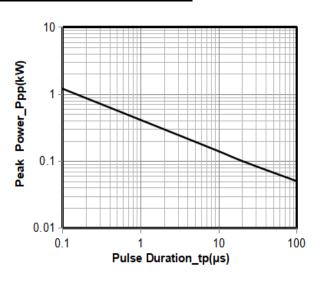
Junction Capacitance vs. Reverse Voltage



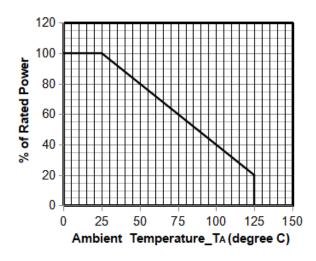
Clamping Voltage vs. Peak Pulse Current



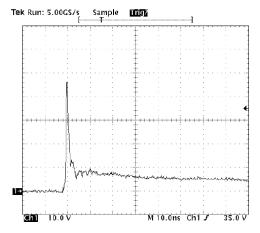
8 X 20µs Pulse Waveform



Peak Pulse Power vs. Pulse Time



Power Derating Curve

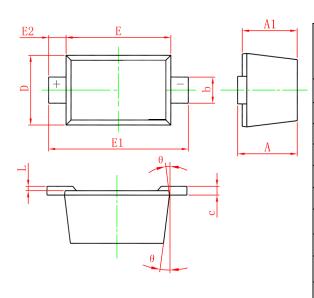


Note: Data is taken with a 10x attenuator

ESD Clamping Voltage 8 kV Contact per IEC61000-4-2

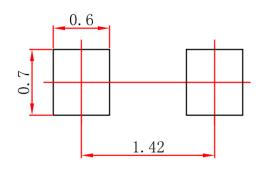


SOD-523 Package Outline Drawing



	DIMENSIONS							
SY M	MILLIMETERS			INCHES				
	MIN	NOM	MAX	MIN	NOM	MAX		
Α	0.51		0.77	0.020		0.031		
A1	0.50		0.70	0.020		0.028		
b	0.25		0.35	0.010		0.014		
С	0.08		0.15	0.003		0.006		
D	0.75		0.85	0.030		0.033		
Е	1.10		1.30	0.043		0.051		
E1	1.50		1.70	0.059		0.067		
E2	0.20REF			0.008REF				
L	0.01		0.07	0.001		0.003		
Θ	7° REF			7° REF				

Suggested Land Pattern



Unit: mm

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Revision, 12/2017 4 of 4

单击下面可查看定价,库存,交付和生命周期等信息

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